

N-channel TrenchMOS standard level FET Rev. 2 — 21 April 2011

Product data sheet

1. **Product profile**

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Suitable for standard level gate drive sources
- **1.3 Applications**
 - 12 V loads
 - Automotive systems

- Suitable for thermally demanding environments due to 175 °C rating
- General purpose power switching

nexperia

Motors, lamps and solenoids

1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	30	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 4</u>	[1]	-	-	75	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	255	W
Static cha	aracteristics						
R _{DSon}	drain-source on-state resistance	$\label{eq:GS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 25 \text{ °C}; \\ \text{see } \underline{\text{Figure 12}}; \text{ see } \underline{\text{Figure 13}} \end{array}$		-	2.9	3.4	mΩ
Avalanch	e ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 75 \text{ A}; \text{V}_{sup} \leq 30 \text{V}; \\ R_{GS} &= 50 \Omega; \text{V}_{GS} = 10 \text{V}; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $		-	-	1.3	J

[1] Continuous current is limited by package.

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		<u>_</u>
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

3. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK763R4-30B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
-			IVIIII	-	
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	30	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	30	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 4</u>	<u>[1]</u> -	75	A
		T_{mb} = 100 °C; V_{GS} = 10 V; see Figure 1	[1] -	75	А
		$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 4}};$	<u>[2][3]</u> _	198	A
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu s$; see <u>Figure 4</u>	-	794	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	255	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	n diode				
ls	source current	T _{mb} = 25 °C	[2][3]	198	Α
			<u>[1]</u> _	75	А
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C	-	794	А
Avalanche ru	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ld} \begin{array}{l} I_{D} = 75 \; A; \; V_{sup} \leq 30 \; V; \; R_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; unclamped \end{array}$	-	1.3	J
E _{DS(AL)R}	repetitive drain-source avalanche energy	see Figure 3	<u>[4][5][6][</u> - <u>7]</u>	-	J

[1] Continuous current is limited by package.

[2] Current is limited by power dissipation chip rating.

[3] Refer to document 9397 750 12572 for further information.

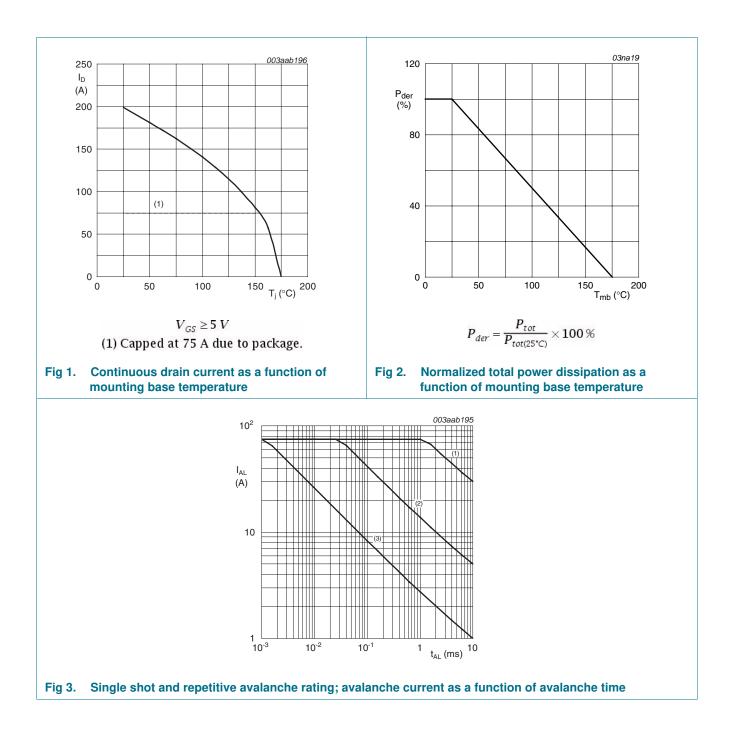
[4] Maximum value not quoted. Repetitive rating defined in avalanche rating figure.

[5] Single-shot avalanche rating limited by maximum junction temperature of 175 °C.

[6] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

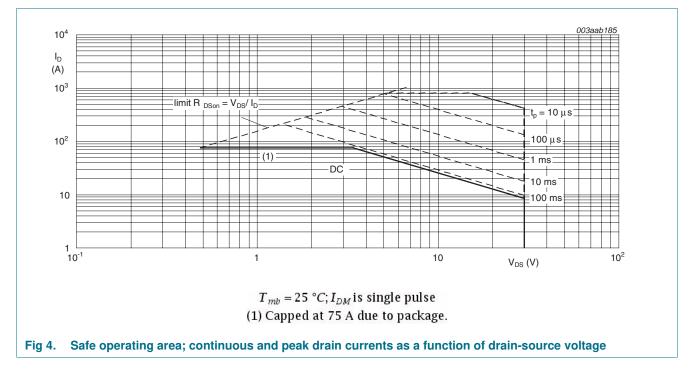
[7] Refer to application note AN10273 for further information.

BUK763R4-30B



BUK763R4-30B

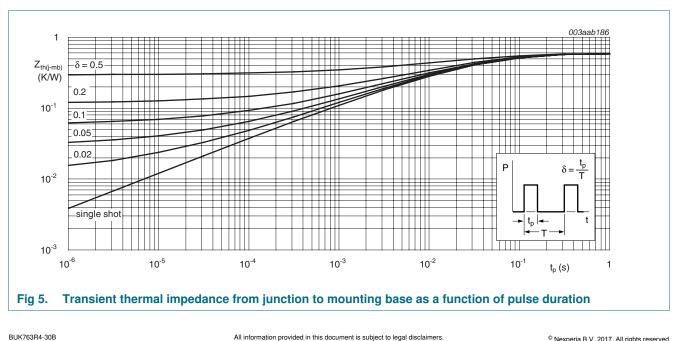
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Thermal characteristics 5.

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base		-	-	0.59	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint; vertical in still air	-	50	-	K/W

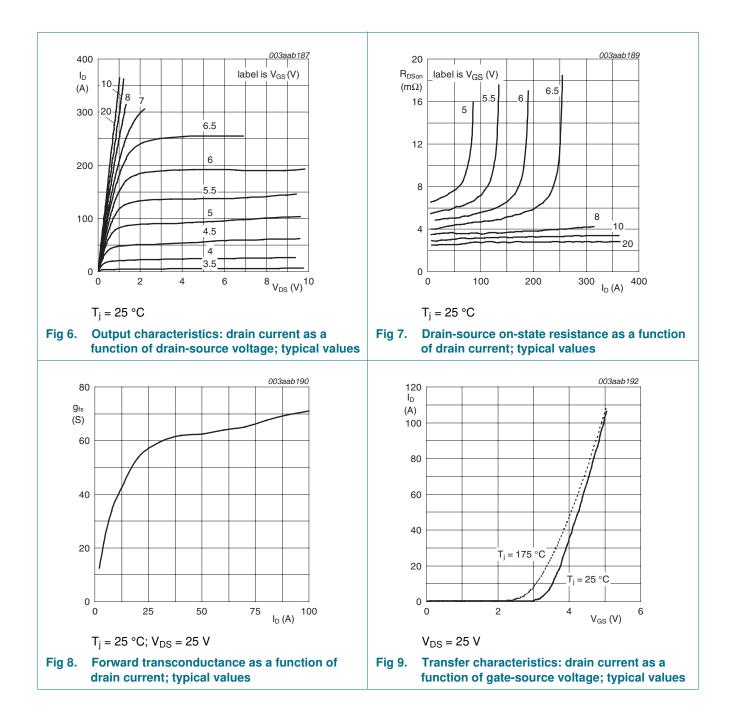


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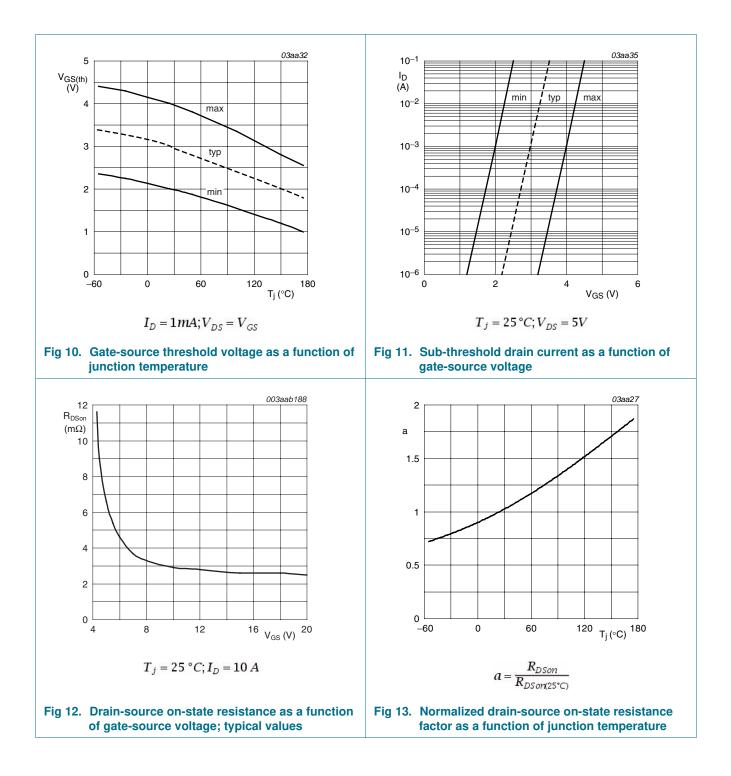
6. Characteristics

	Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	-	racteristics					
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$			I _D = 250 μA; V _{GS} = 0 V; T _i = 25 °C	30	-	-	V
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	(2.1)200			27	-	-	V
voltage see Figure 10; see Figure 11 I - - loss drain leakage current Vos = 30 V; Vos = 0 V; Tj = 25 °C - 0.05 10 loss gate leakage current Vos = 30 V; Vos = 0 V; Tj = 25 °C - 2 100 Roso drain leakage current Vos = 20 V; Vos = 0 V; Tj = 25 °C - 2 100 Roso drain-source on-state ese Figure 12; see Figure 13 - - 6.5 Poss drain leakage current Vos = 30 V; Vos = 0 V; Tj = 25 °C - 2.9 3.4 loss drain leakage current Vos = 30 V; Vos = 0 V; Tj = 175 °C - - 6.5 loss drain leakage current Vos = 30 V; Vos = 0 V; Tj = 175 °C - 2.9 3.4 loss drain leakage current Vos = 30 V; Vos = 0 V; Tj = 175 °C - - 500 Dynamic characteristics - see Figure 14 - - 75 - Octo gate-drain charge Io = 25 A; Vos = 25 V; F = 1 MHz; - 3713 4951 </td <td>V_{GS(th)}</td> <td>-</td> <td></td> <td>2</td> <td>3</td> <td>4</td> <td>V</td>	V _{GS(th)}	-		2	3	4	V
	V _{GSth}			-	-	4.4	V
				1	-	-	V
$ \begin{array}{ c c c c c c } \hline V_{GS} = -20 \ V; \ V_{DS} = 0 \ V; \ T_{j} = 25 \ ^{\circ}\ C & - & 2 & 100 \\ \hline V_{GS} = 10 \ V; \ I_{D} = 25 \ A; \ T_{j} = 175 \ ^{\circ}\ C; & - & - & 6.5 \\ \hline see \ Figure 12; \ see \ Figure 13 & V_{GS} = 10 \ V; \ I_{D} = 25 \ A; \ T_{j} = 25 \ ^{\circ}\ C; & - & - & 500 \\ \hline Dynamic \ characteristics & & & & & & & & & & & & & & & & & & &$	I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
	I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
$ \begin{array}{ c c c c } & \text{resistance} & \begin{array}{ c c } & \text{see Figure 12} \\ \hline & V_{GS} = 10 \ V; \ _{D} = 25 \ A; \ T_{J} = 25 \ ^{\circ}\text{C}; \\ & \text{see Figure 13} \\ \hline & V_{DS} = 30 \ V; \ V_{GS} = 0 \ V; \ T_{J} = 175 \ ^{\circ}\text{C} & - & - & 500 \\ \hline & \text{Dynamic characteristics} \\ \hline & & & & & & & & & & & & & & & & & &$			V _{GS} = -20 V; V _{DS} = 0 V; T _i = 25 °C	-	2	100	nA
$see Figure 12; see Figure 13$ $l_{DSS} drain leakage current V_{DS} = 30 V; V_{GS} = 0 V; T_j = 175 °C - 500$ $\begin{array}{c c c c c c } \hline Dynamic characteristics \\ \hline Q_{G(tot)} total gate charge I_D = 25 A; V_{DS} = 24 V; V_{GS} = 10 V; - 75 - 986 Figure 14 - 19 - 986 Figure 15 - 1249 - 1499 - 986 Figure 15 - 1249 - 1499 - 986 Figure 15 - 1249 - 1499 - 1499 Figure 15 - 1249 - 1499 Figure 16 - 71 - 1249 Figure 16 - 71 - 71 - 71 - 71 - 71 - 71 - 71 -$	R _{DSon}			-	-	6.5	mΩ
Dynamic characteristics $Q_{G(tot)}$ total gate charge $I_D = 25 \text{ Å; } V_{DS} = 24 \text{ V; } V_{GS} = 10 \text{ V;}$ see Figure 14-75- Q_{GS} gate-source charge-2319- Q_{GD} gate-drain charge-2323- C_{iss} input capacitance $V_{GS} = 0 \text{ V; } V_{DS} = 25 \text{ V; } f = 1 \text{ MHz;}$ $T_j = 25 \text{ °C; see Figure 15}$ -12491499 C_{rss} reverse transfer capacitance-460630 C_{rss} reverse transfer capacitance-460630 $t_{d(on)}$ turn-on delay time $V_{DS} = 30 \text{ V; } R_L = 1.2 \Omega; V_{GS} = 10 \text{ V;}$ $T_j = 25 \text{ °C;}$ -32- $t_{d(on)}$ turn-off delay time $V_{DS} = 30 \text{ V; } R_L = 1.2 \Omega; V_{GS} = 10 \text{ V;}$ $T_j = 71 \text{ or } 0.889 \text{ or } 0.283 \text{ or } 0.28$				-	2.9	3.4	mΩ
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Dynamic o	haracteristics					
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$	-	75	-	nC
$\begin{array}{c c c c c c c } \hline V_{GS} = 0 \ V; \ V_{DS} = 25 \ V; \ f = 1 \ MHz; & & & & & & & & & & & & & & & & & & &$	Q _{GS}	gate-source charge	see Figure 14	-	19	-	nC
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Q _{GD}	gate-drain charge		-	23	-	nC
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	C _{iss}	input capacitance		-	3713	4951	pF
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 15</u>	-	1249	1499	pF
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				-	460	630	pF
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	t _{d(on)}	turn-on delay time		-	32	-	ns
$f_{f} = fall time + fall time + from contact screw on mounting base to centre of die + from upper edge of drain mounting base to centre of die + from upper edge of drain mounting base to centre of die + from drain lead 6 mm from package to centre of die + from source lead to source bonding + from source + from source lead to source bonding + from source + from sourc$	t _r	rise time	$R_{G(ext)} = 10 \ \Omega$	-	64	-	ns
$ \begin{array}{c} L_{D} \\ L_{D} $	t _{d(off)}	turn-off delay time		-	89	-	ns
$ \begin{array}{c} \mbox{inductance} \\ \mbox{inductance} $	t _f	fall time		-	71	-	ns
to centre of diefrom drain lead 6 mm from package to centre of die-4.5-Lsinternal source inductancefrom source lead to source bonding pad-7.5-Source-drain diodeV_{SD}source-drain voltageI_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; see Figure 16-0.851.2trrreverse recovery timeI_S = 20 A; dIs/dt = -100 A/µs; V_{GS} = 0 V; C =70-	L _D		•	-	3.5	-	nH
centre of dieL_Sinternal source inductancefrom source lead to source bonding pad-7.5-Source-drain diodeIS = 25 A; V_{GS} = 0 V; T_j = 25 °C; see Figure 16-0.851.2trrreverse recovery timeIS = 20 A; dIS/dt = -100 A/µs; V_{GS} = 0 V; $- 70$ -70-				-	2.5	-	nH
inductancepadSource-drain diode V_{SD} source-drain voltage $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ -0.851.2 see Figure 16- $I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A}/\mu s; V_{GS} = 0 \text{ V};$ -70-				-	4.5	-	nH
$V_{SD} \qquad source-drain voltage \qquad I_{S} = 25 \text{ A}; V_{GS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}; \qquad - \qquad 0.85 \qquad 1.2$ $see \frac{Figure 16}{I_{S}} \qquad reverse recovery time \qquad I_{S} = 20 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \qquad - \qquad 70 \qquad - \qquad$	L _S			-	7.5	-	nH
see Figure 16 I_{Srr} reverse recovery time $I_S = 20 \text{ A}; \text{ dI}_S/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ - 70 -	Source-dr	ain diode					
	V _{SD}	source-drain voltage		-	0.85	1.2	V
	t _{rr}	reverse recovery time		-	70	-	ns
Q_r recovered charge $V_{DS} = 30$ V - 58 -	Q _r	recovered charge	V _{DS} = 30 V	-	58	-	nC
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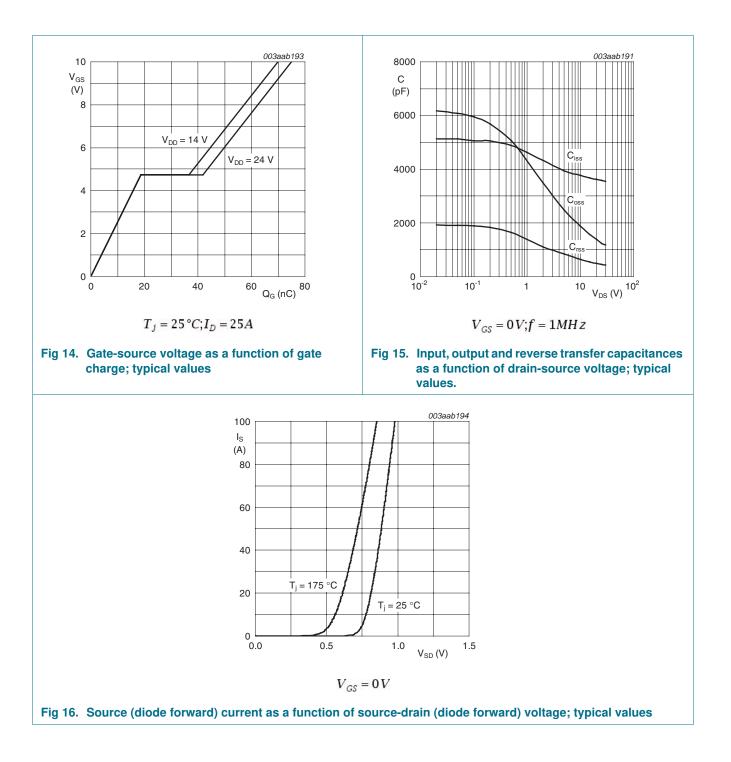
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7. Package outline

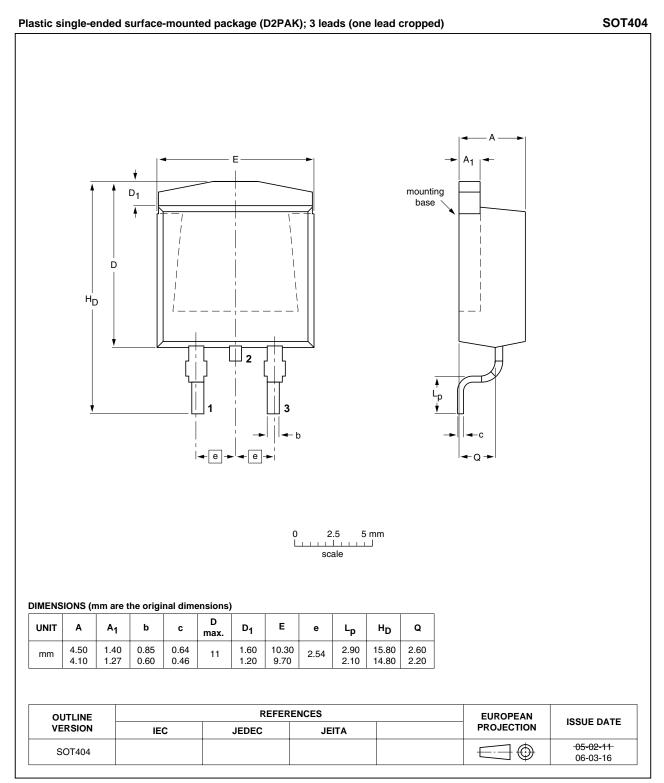


Fig 17. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7. Revision hi	istory				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
BUK763R4-30B v.2	20110421	Product data sheet	-	BUK75_763R4-30B_1	
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 				
	 Legal texts have b 	een adapted to the new c	company name where ap	propriate.	
	 Type number BUK 	763R4-30B separated fro	om data sheet BUK75_7	63R4-30B_1.	
BUK75_763R4-30B_1	20060105	Product specification	-	-	

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status 3	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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